

Amendments to the Claims:

Please amend claims 1 and 2 as follows.

This listing of claims replaces all prior versions, and listings, of claims in the application.

Listing of claims:

1. (currently amended) An electrode line structure of a semiconductor device comprising:
a semiconductor substrate; and
electrode lines on the semiconductor substrate, the electrode lines each having an inclined outer end in the long axis direction;
wherein the electrode lines each include a first line unit, which substantially functions as an electrode line, a second line unit, which includes the inclined outer end in the long axis direction and which is separated from the first line unit by a predetermined distance, and an insulating plug, which is interposed between the first line unit and the second line unit and electrically insulates the first line unit from the second line unit, an upper surface of the second line unit being of uniform height above the substrate over the entire length of the second line unit between the insulating plug and the inclined outer end.
2. (currently amended) The electrode line structure of claim 1, wherein a first length (X1) of the electrode lines is greater than a second length (X2) ~~of conventional electrode lines~~ by at least a predetermined third length (X3).
3. (previously presented) The electrode line structure of claim 2, wherein the insulating plug is formed at a predetermined position of each of the electrode lines such that the first line unit has the second length (X2).

4. (previously presented) The electrode line structure of claim 2, wherein the third length (X3) is the length of the second line unit and is greater than a width of the electrode lines and less than the second length (X2).

5. (original) The electrode line structure of claim 1, wherein the first line unit and the second line unit each comprise a conductive layer and a hard mask layer, respectively.

6. (original) The electrode line structure of claim 5, wherein the conductive layer comprises a material containing tungsten.

7. (original) The electrode line structure of claim 5, wherein the hard mask layer comprises a silicon nitride layer or a silicon oxynitride layer.

8. (previously presented) The electrode line structure of claim 1, wherein a spacer is formed on the inclined outer end in the long axis direction of the second line unit.

9. (original) The electrode line structure of claim 8, wherein the insulating plug is formed of a material of which the spacer is formed.

10. (original) The electrode line structure of claim 1, wherein the electrode lines comprise one of word lines and bit lines.

11. - 18. (canceled)